

isc Silicon NPN RF Transistor
2SC5064
DESCRIPTION

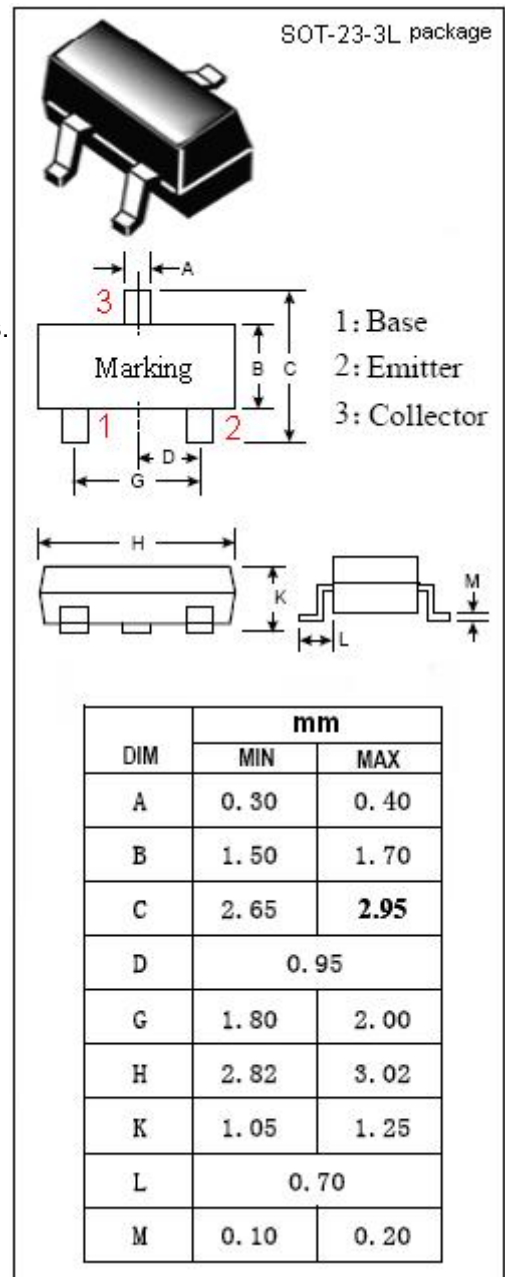
- Low Noise and High Gain
 $NF = 1.1 \text{ dB TYP.}, |S_{21e}|^2 = 12 \text{ dB TYP.}$
 $@V_{CE} = 5 \text{ V}, f = 1.0 \text{ GHz}$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for VHF~UHF band low noise amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 20 | V |
| V_{CEO} | Collector-Emitter Voltage | 12 | V |
| V_{EBO} | Emitter-Base Voltage | 3.0 | V |
| I_C | Collector Current-Continuous | 30 | mA |
| I_B | Base Current-Continuous | 15 | mA |
| P_C | Collector Power Dissipation @ $T_c=25^\circ\text{C}$ | 0.15 | W |
| T_J | Junction Temperature | 125 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~125 | $^\circ\text{C}$ |



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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---------------------------------|--------------------------------|--|-----|------|-----|------|
| I _{CBO} | Collector Cutoff Current | V _{CB} = 10V; I _E = 0 | | | 1.0 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 1V; I _C = 0 | | | 1.0 | μ A |
| h _{FE} | DC Current Gain | I _C = 10mA ; V _{CE} = 5V | 80 | | 240 | |
| f _T | Current-Gain—Bandwidth Product | I _C = 10mA ; V _{CE} = 5V | 5 | 7 | | GHz |
| C _{re} | Feed-Back Capacitance | I _E = 0 ; V _{CB} = 5V; f= 1.0MHz | | 0.45 | 0.9 | pF |
| C _{OB} | Output Capacitance | I _E = 0 ; V _{CB} = 5V; f= 1.0MHz | | 0.7 | | pF |
| S _{21e} ² | Insertion Power Gain | I _C = 10mA ; V _{CE} = 5V;f= 500MHz | | 17 | | dB |
| S _{21e} ² | Insertion Power Gain | I _C = 10mA ; V _{CE} = 5V;f= 1.0GHz | 8.5 | 12 | | dB |
| NF | Noise Figure | I _C = 3mA ; V _{CE} = 5V;f= 500MHz | | 1 | | dB |
| NF | Noise Figure | I _C = 3mA ; V _{CE} = 5V;f= 1.0GHz | | 1.1 | 2.0 | dB |

◆ h_{FE} Classification

| | |
|--------|---------|
| O | Y |
| 80-160 | 120-240 |

**NOTICE:**

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